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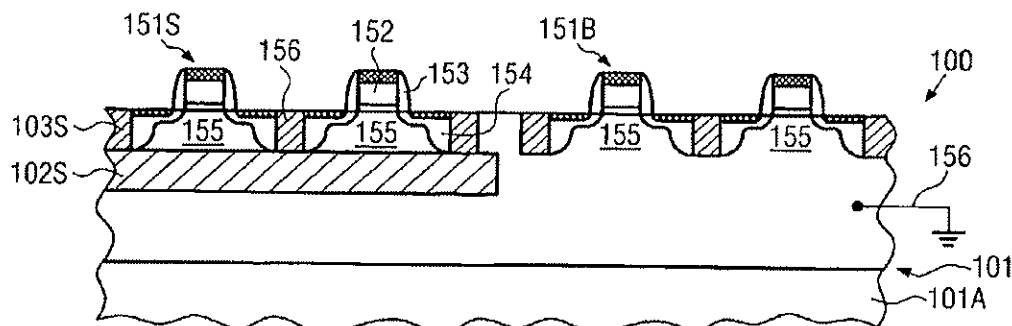
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ning of each regular issue of the PCT Gazette.

(54) Title: SEMICONDUCTOR DEVICE COMPRISING SOI TRANSISTORS AND BULK TRANSISTORS AND A METHOD OF FORMING THE SAME



(57) Abstract: By forming bulk-like transistors (151B) in sensitive RAM areas of otherwise SOI-based CMOS circuits, a significant savings in valuable chip area may be achieved since the RAM areas may be formed on the basis of a bulk transistor configuration, thereby eliminating hysteresis effects that may typically be taken into consideration by providing transistors of increased transistor width or by providing body ties. Hence, the benefit of high switching speed may be maintained in speed-critical circuitry, such as CPU cores, while at the same time the RAM circuit may be formed in a highly space-efficient manner.